

Technical Data
Data Sheet N1009, Rev. C

Green Products

209CMQ135/209CMQ150 SCHOTTKY RECTIFIER

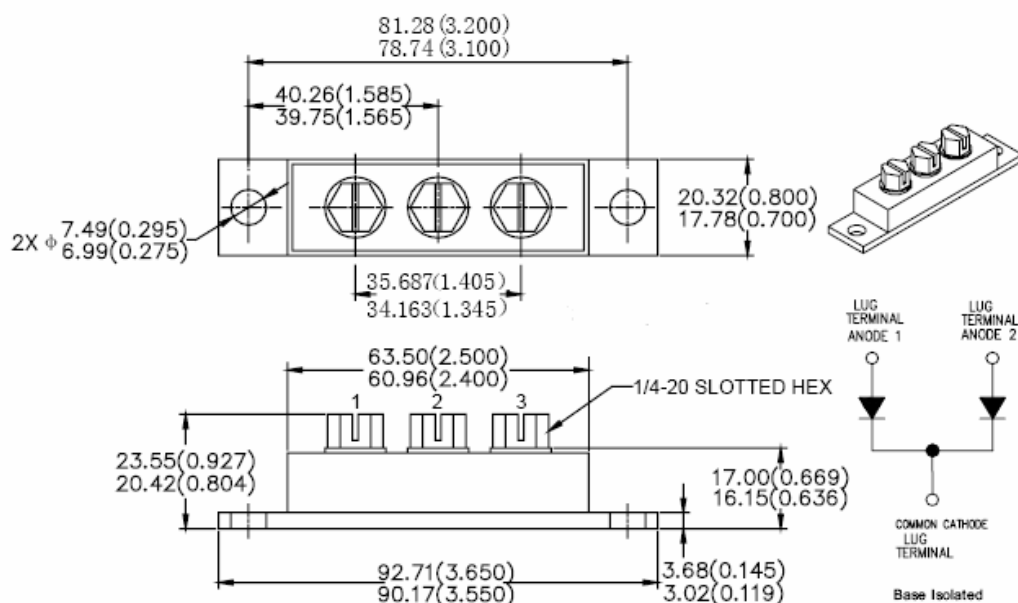
Applications:

- High current switching power supply • Plating power supply • Free-Wheeling diodes
- Reverse battery protection • Converters • UPS System • Welding

Features:

- 175 °C T_J operation
- Center tap module
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm/Inches



Please Note: Anode 1 = Terminal 1; Anode 2 = Terminal 3; Common Cathode = Terminal 2
Suffix R Denotes for Reversed Polarity.

PRM4 (Isolated)

MARKING, MOLDING RESIN

Marking for 209CMQ135/150, 1st row SS YYWWL, 2nd row 209CMQ135/150

Where YY is the manufacture year

WW is the manufacture week code

L is the wafer's Lot Number

Molding resin

Epoxy resin UL:94V-0

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	135(209CMQ135) 150(209CMQ150)	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=110^{\circ}C$, rectangular wave form	100 per leg 200 per device	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	1440	A

Electrical Characteristics:

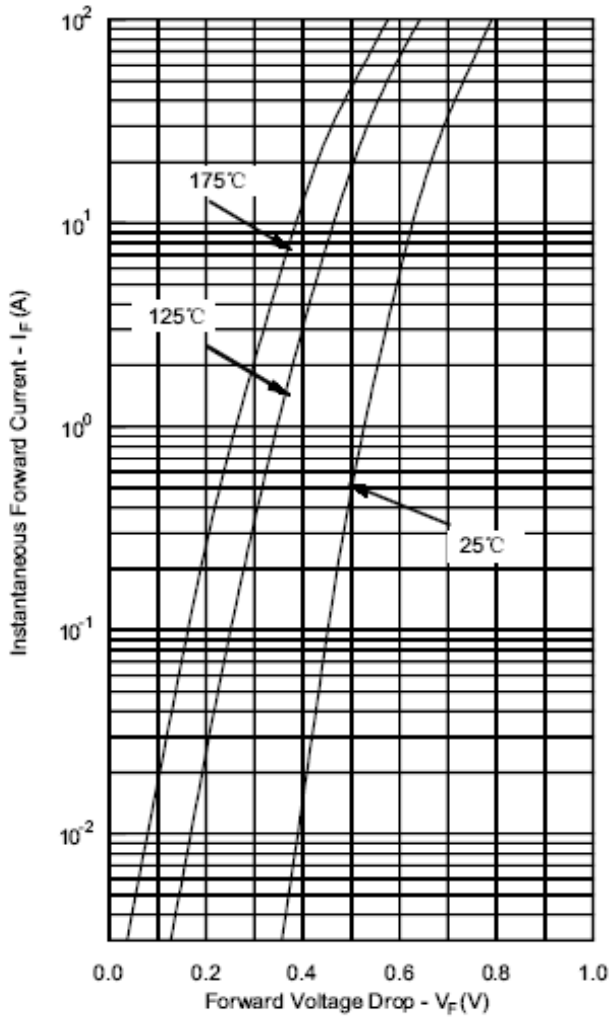
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 100A, Pulse, $T_J = 25^{\circ}C$ @ 200A, Pulse, $T_J = 25^{\circ}C$	1.03 1.22	V
	V_{F2}	@ 100A, Pulse, $T_J = 125^{\circ}C$ @ 200A, Pulse, $T_J = 125^{\circ}C$	0.71 0.82	V
Max. Reverse Current at DC condition	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25^{\circ}C$	3	mA
Max. Reverse Current	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125^{\circ}C$	45	mA
Max. Junction Capacitance	C_T	@ $V_R = 5V$, $T_C = 25^{\circ}C$ $f_{SIG} = 1MHz$	3000	pF
Max. Voltage Rate of Change(Rated V_R)	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

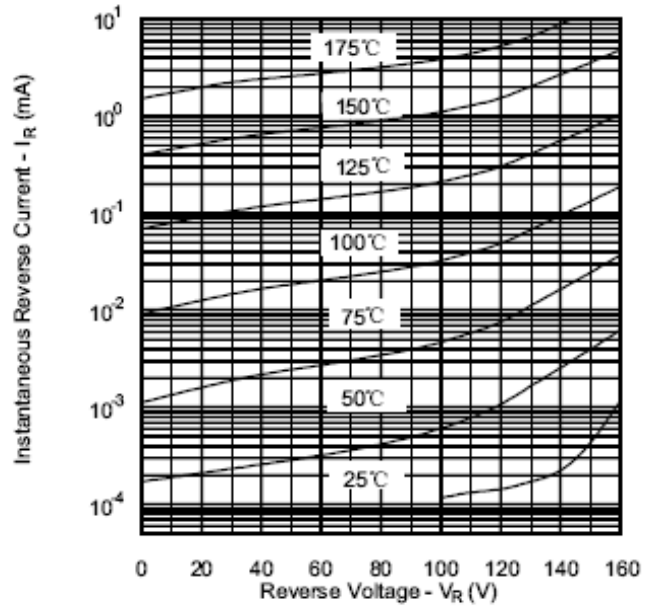
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units	
Max. Junction Temperature	T_J	-	-55 to +175	$^{\circ}C$	
Max. Storage Temperature	T_{stg}	-	-55 to +175	$^{\circ}C$	
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	0.7	$^{\circ}C/W$	
Maximum Thermal Resistance Junction to Case (per device)	$R_{\theta JC}$	DC operation	0.35	$^{\circ}C/W$	
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.10	$^{\circ}C/W$	
Mounting Torque	T_M	-	Mounting Torque	24(min) 35(max)	Kg-cm
			Terminal Torque	35(min) 46(max)	
Approximate Weight	wt	-	79	g	
Case Style	PRM4 (Isolated)				

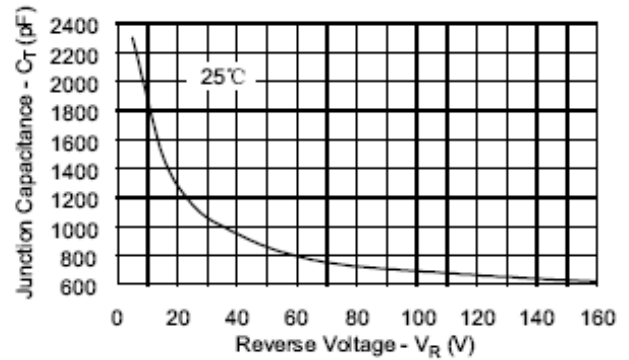
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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